

ABSTRACT OF THE DISCLOSURE

[0035] A method and mask to improve measurement of alignment marks is disclosed. An exemplary embodiment of the invention includes a resist mask with a patterned alignment mark comprising an assemblage of features whose spacing is smaller than the wavelength of light used to measure the alignment. In a preferred embodiment, an alignment mark patterning process alters the appearance of the alignment mark and renders an enhanced contrast with the substrate background.

Document #: 1252621 v.1